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REPLACED

IR-1175

THREE-TERMINAL THYRISTOR WITH SINGLE  
MOS-GATE CONTROLLED CHARACTERISTICS

ABSTRACT OF THE DISCLOSURE

5 A MOS-controlled thyristor which has current saturation characteristics and does not have any parasitic thyristor structure. The device requires only a single gate drive and is a three terminal device. The device can be constructed in a cellular geometry. In all embodiments, the device has superior turn-off characteristics and a wider Safe-Operating-Area because the  $N^{++}$  emitter/P base junction is reverse biased during turn-off.